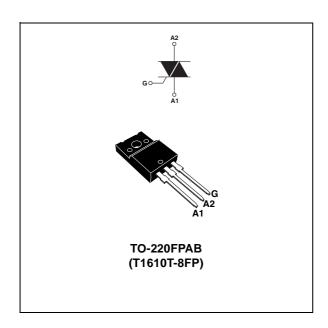


16 A logic level Triac

Datasheet - production data



Description

Available in through-hole fullpack package, the T1610T-8FP Triac can be used for the on/off or phase angle control function in general purpose AC switching. This device can be directly driven by a microcontroller thanks to its 10 mA gate current requirement.

Provides UL certified insulation rated at 1500 V rms.

Table 1. Device summary

Symbol	Value	Unit
I _{T(rms)}	16	Α
V_{DRM}, V_{RRM}	800	V
V_{DSM}, V_{RSM}	900	V
I _{GT}	10	mA

Features

- Medium current Triac
- Three triggering quadrants Triac
- ECOPACK®2 compliant component
- Complies with UL standards (File ref: E81734)
- 16 A high performance Triac:
 - High T_i family
 - High dl/dt family
 - High dV/dt family

Applications

- · General purpose AC line load switching
- · Motor control circuits
- Small home appliances
- Lighting
- · Inrush current limiting circuits
- · Overvoltage crowbar protection

Characteristics T1610T-8FP

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Table 2. Absolute ratings (limiting values, $T_j = 25$ °C unless otherwise stated)

Symbol	Paramete	Value	Unit		
I _{T(rms)}	On-state rms current (full sine wave	T _C = 87 °C	16	Α	
l	Non repetitive surge peak on-state	F = 50 Hz	t = 20 ms	120	Α
I _{TSM}	current (full cycle, T _j initial = 25 °C)	F = 60 Hz	t = 16.7 ms	126	^
l ² t	I^2 t value for fusing, T_j initial = 25 °C		$t_p = 10 \text{ ms}$	95	A ² s
V _{DRM} ,	Repetitive surge peak off-state volta	ae	T _j = 150 °C	600	V
V_{RRM}	Trepetitive surge peak oil-state voita	T _j = 125 °C	800	V	
V _{DSM} , V _{RSM}	Non repetitive surge peak off-state voltage $t_p =$			900	V
dI/dt	Critical rate of rise of on-state currer $I_G = 2 \times I_{GT}$, $t_r \le 100 \text{ ns}$	F = 100 Hz	100	A/µs	
I _{GM}	Peak gate current	t _p = 20 μs	T _j = 150 °C	4	Α
P _{G(AV)}	Average gate power dissipation $T_j = 150 \text{ °C}$			1	W
T _{stg}	Storage junction temperature range			- 40 to + 150	°C
T _j	Operating junction temperature range			- 40 to + 150	
T _L	Maximum lead temperature for soldering during 10 s			260	°C
V _{ins}	Insulation rms voltage, 1 minute			1500	V

Table 3. Electrical characteristics ($T_j = 25$ °C, unless otherwise specified)

Symbol	Test conditions Quadrant			Value	Unit
1.	$V_D = 12 \text{ V}, R_L = 30 \Omega$	1 - 11 - 111	Min.	0.5	mA
I _{GT}		1 - 11 - 111	Max.	10	
V _{GT}	$V_D = 12 \text{ V}, R_L = 30 \Omega$	1 - 11 - 111	Max.	1.3	V
V _{GD}	$V_D = V_{DRM}, R_L = 3.3 \text{ k } \Omega \text{ T}_j = 150 \text{ °C}$	1 - 11 - 111	Min.	0.2	V
I _H ⁽¹⁾	I _T = 500 mA		Max.	15	mA
	I _G = 1.2 I _{GT}	1 - 111	Max.	20	- mA
l _L		II		25	
dV/dt ⁽¹⁾	V _D = V _R = 536 V, gate open	T _j = 125 °C	Min.	250	V/µs
u v/ui.	V _D = V _R = 402 V, gate open	T _j = 150 °C	IVIIII.	170	V/µs
(dl/dt)c (1)	(dV/dt)c = 0.1 V/µs	T _j = 125 °C	Min.	21.6	A/ms
(ui/ut)C (**)		T _j = 150 °C		15.1	
(dl/dt)c ⁽¹⁾	(dV/dt)c = 10 V/μs	T _j = 125 °C	Min.	11.3	A/ms
(al/at)c ⁽¹⁾		T _j = 150 °C		5.0	

^{1.} For both polarities of A2 referenced to A1

T1610T-8FP Characteristics

Table	4	Static c	harac	teristics
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Symbol	Test conditions			Value	Unit
V _T ⁽¹⁾	I _{TM} = 22.6 A, t _p = 380 μs	T _j = 25 °C	Max.	1.55	V
V _{t0} (1)	Threshold voltage	T _j = 150 °C	Max.	0.85	V
R _d ⁽¹⁾	Dynamic resistance	T _j = 150 °C	Max.	27	mΩ
	V - V - 800 V	T _j = 25 °C	- Max.	7.5	μA
I _{DRM} I _{RRM}	$V_{DRM} = V_{RRM} = 800 \text{ V}$	T _j = 125 °C	iviax.	1	mA
'KKIVI	V _{DRM} = V _{RRM} = 600 V	T _j = 150 °C	Max.	3.0	IIIA

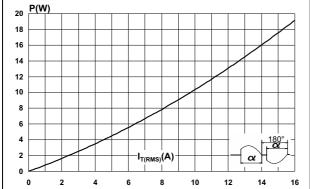
^{1.} For both polarities of A2 referenced to A1

Table 5. Thermal resistance

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (AC)	3.3	°C/W
R _{th(j-a)}	Junction to ambient (DC)	60	°C/W

Figure 1. Maximum power dissipation versus on-state rms current (full cycle)

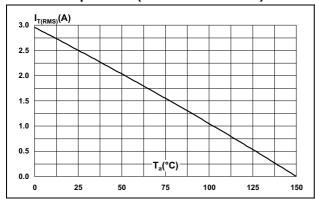
Figure 2. On-state rms current versus case temperature (full cycle) 18 | I_{T(RMS)}(A) 16 14 12

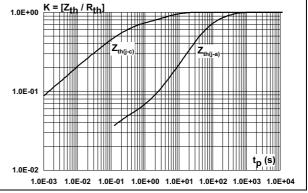


10 T_c(°C)

Figure 3. On-state rms current versus ambient temperature (free air convection)

Figure 4. Relative variation of thermal impedance versus pulse duration

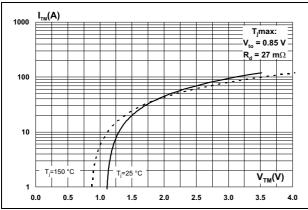




Characteristics T1610T-8FP

Figure 5. On-state characteristics (maximum values)

Figure 6. Surge peak on-state current versus number of cycles



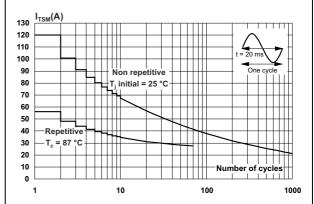
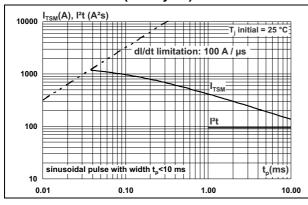


Figure 7. Non repetitive surge peak on-state current and corresponding values of I²t (half cycle)

Figure 8. Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)



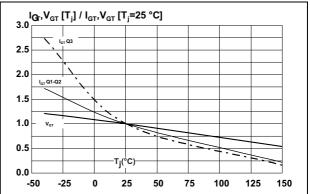
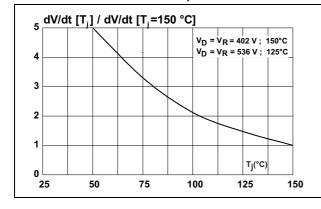
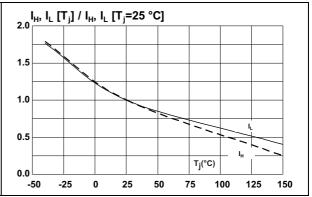


Figure 9. Relative variation of static dV/dt immunity versus junction temperature (typical values)

Figure 10. Relative variation of holding and latching current versus junction temperature (typical values)

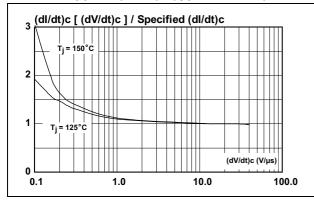




T1610T-8FP Characteristics

Figure 11. Relative variation of critical rate of decrease of main current (di/dt)c versus reapplied (dV/dt)c (typical values)

Figure 12. Relative variation of critical rate of decrease of main current (di/dt)c versus junction temperature (typical values)



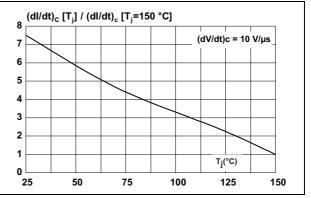
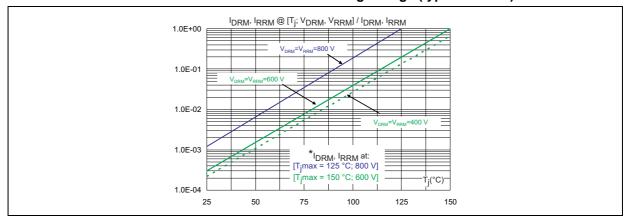


Figure 13. Relative variation of leakage current versus junction temperature for different values of blocking voltage (typical values)



Package information T1610T-8FP

2 Package information

- Epoxy meets UL94, V0
- Lead-free package
- Recommended torque: 0.4 to 0.6 N·m

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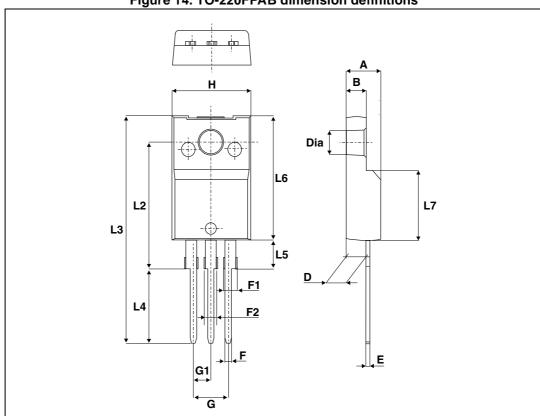


Figure 14. TO-220FPAB dimension definitions

T1610T-8FP Package information

Table 6. TO-220FPAB dimension values

		Dimensions				
Ref.	Millin	neters	Inc	hes		
	Min.	Max.	Min.	Max.		
А	4.4	4.6	0.173	0.181		
В	2.5	2.7	0.098	0.106		
D	2.5	2.75	0.098	0.108		
E	0.45	0.70	0.018	0.027		
F	0.75	1	0.030	0.039		
F1	1.15	1.70	0.045	0.067		
F2	1.15	1.70	0.045	0.067		
G	4.95	5.20	0.195	0.205		
G1	2.4	2.7	0.094	0.106		
Н	10	10.4	0.393 0.40			
L2	16 ⁻	Тур.	0.63	Тур.		
L3	28.6	30.6	1.126	1.205		
L4	9.8	10.6	0.386	0.417		
L5	2.9	3.6	0.114	0.142		
L6	15.9	16.4	0.626	0.646		
L7	9.00	9.30	0.354	0.366		
Dia.	3.00	3.20	0.118	0.126		

Ordering information T1610T-8FP

3 Ordering information

Figure 15. Ordering information scheme

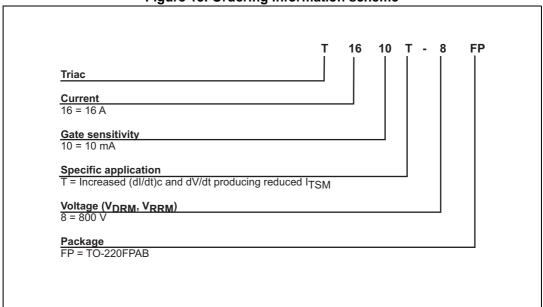


Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T1610T-8FP	T1610T-8FP	TO-220FPAB	2.0 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
05-Feb-2014	1	Initial release.

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